
2SC4366

Silicon NPN Epitaxial

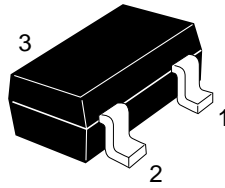
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Application

Low Frequency amplifier

Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector

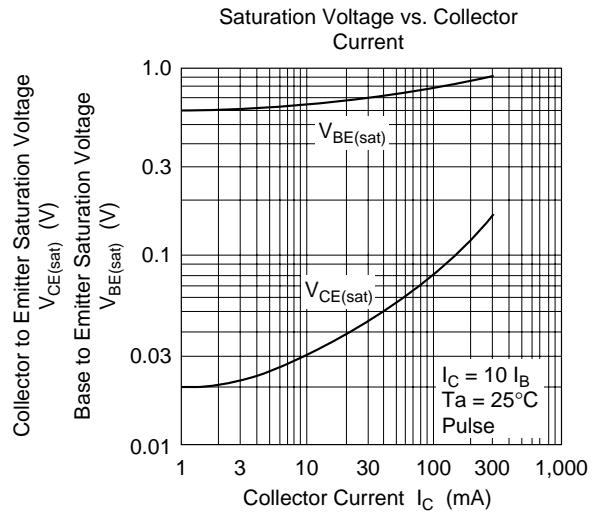
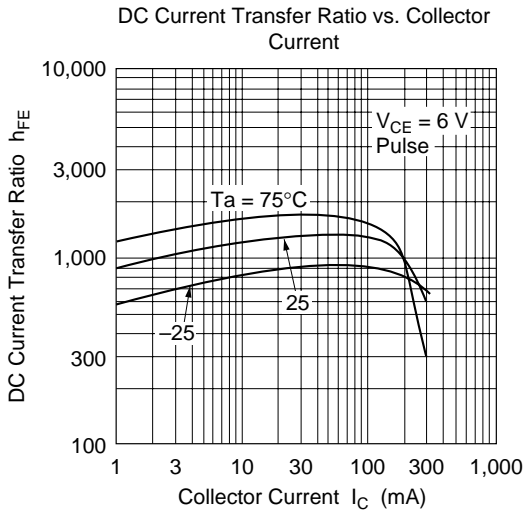
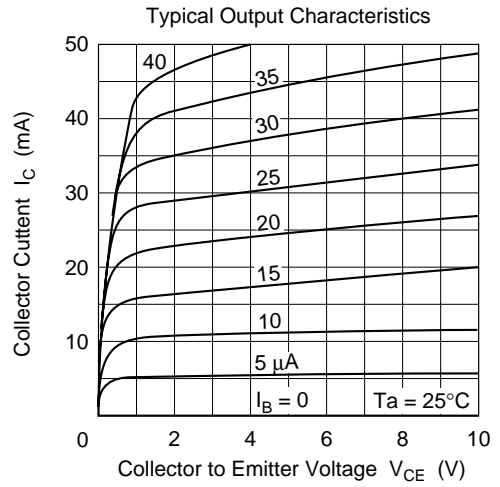
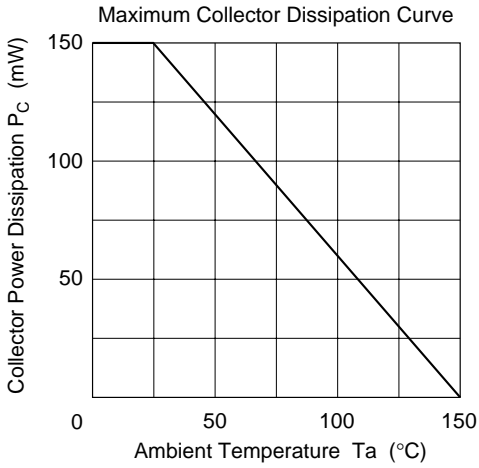
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	60	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	15	V
Collector current	I_{C}	300	mA
Collector power dissipation	P_{C}	150	mW
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

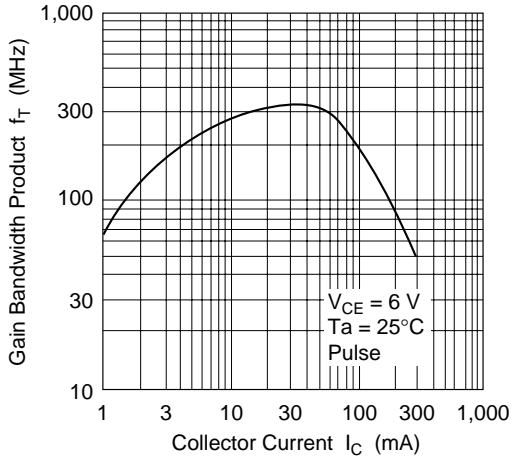
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	60	—	—	V	$I_{\text{C}} = 10 \mu\text{A}$, $I_{\text{E}} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	50	—	—	V	$I_{\text{C}} = 1 \text{ mA}$, $R_{\text{BE}} = \infty$
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	15	—	—	V	$I_{\text{E}} = 10 \mu\text{A}$, $I_{\text{C}} = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{\text{CB}} = 50 \text{ V}$, $I_{\text{E}} = 0$
Base to emitter voltage	V_{BE}	—	—	0.75	V	$V_{\text{CE}} = 6 \text{ V}$, $I_{\text{C}} = 1 \text{ mA}$
DC current transfer ratio	h_{FE1}	800	—	2000		$V_{\text{CE}} = 6 \text{ V}$, $I_{\text{C}} = 100 \text{ mA}$ (pulse)
	h_{FE2}	500	—	—		$V_{\text{CE}} = 6 \text{ V}$, $I_{\text{C}} = 1 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE}(\text{sat})}$	—	—	0.3	V	$I_{\text{C}} = 300 \text{ mA}$, $I_{\text{B}} = 30 \text{ mA}$ (pulse)

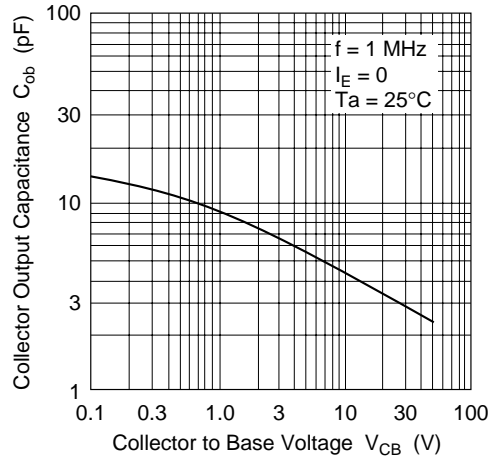
Note: Marking is "Z1-".

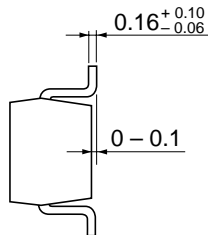
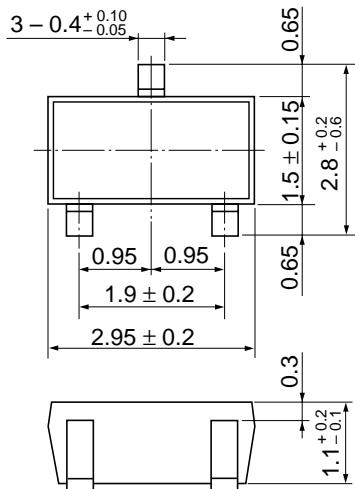


Gain Bandwidth Product vs. Collector Current



Collector Output Capacitance vs. Collector to Base Voltage





Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.011 g

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